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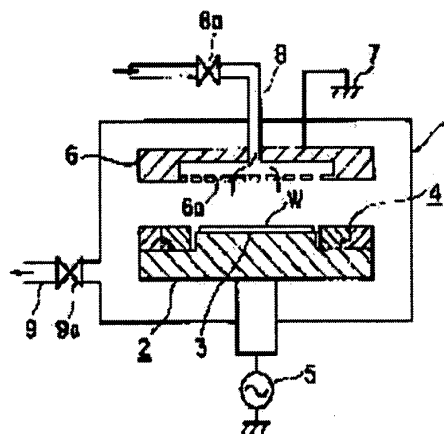
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(54) PLASMA ETCHING SYSTEM

(57)Abstract:

PURPOSE: To provide a plasma etching system that achieves the improved uniformity in etching rate across the entire surface of a workpiece, and that is capable of easily coping with any change to etching process conditions for such improved uniformity in etching rate.

CONSTITUTION: With the plasma etching system a semiconductor wafer is etched as follows: The semiconductor wafer is placed in a vacuum processing vessel 1, and process gas is introduced into the vessel. High-frequency voltage is applied between a lower electrode 2 and an upper electrode 6 to produce plasma, and the wafer is thereby etched. In this plasma etching system, a focus ring 4 placed on the periphery of the workpiece support section 3 of the lower electrode 2, is of composite structure, wherein an exposed tungsten member is placed on the circumference of the focus ring 4.



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